TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP124

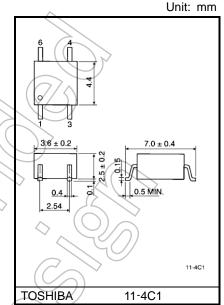
Programmable Controllers AC / DC-Input Module Solid-State Relays

The TOSHIBA mini flat coupler TLP124 is a small outline coupler, suitable for a surface mount assembly.

TLP124 consists of a photo transistor optically coupled to a gallium arsenide infrared emitting diode.

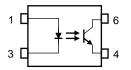
- Collector-emitter voltage: 80 V (min)
- Current transfer ratio: 100% (min)
 Rank BV: 200% (min)
- Isolation voltage: 3750 Vrms (min)
- UL recognized: UL1577, file No. E67349
- c-UL approved :CSA Component Acceptance Service

No. 5A, File No.E67349



Weight: 0.09g (typ.)

Pin Configurations (top view)



- 1 : Anode
- 3: Cathode
- 4 : Emitter
- 6 : Collector

Start of commercial production 1988-04

TLP124

Current Transfer Ratio

Classification	Cu			
	Ta = 25°C		Ta = -25 to 75°C	Marking of
(Note 1)		IF = 0.5 mA VCE = 1.5 V	IF = 1 mA VCE = 0.5 V	Classification
Rank BV	200%	100%	100%	BV
Standard	100%	50%	50%	BV, Blank

Note 1: Ex, rank BV: TLP124(BV)

Note: Application type name for certification test, please use standard product type name, i, e.

TLP124(BV): TLP124

Absolute Maximum Ratings (Ta = 25°C)

				\
	Characteristic	Symbol	Rating	Unit
	Forward current	lF	50	mA
	Forward current derating (Ta ≥ 53°C)	ΔI _F /°C	-0.7	mA/°C
LED	Peak forward current (100 µs pulse, 100 pps)	I _{FP}	1	A
l "	Reverse voltage	VR <	5	
	Diode power dissipation	PD	100	mW/
	Diode power dissipation derating $\mbox{(Ta} \geq 53\mbox{°C)} \label{eq:Ta}$	ΔP _D /°C	-1.39	mW/°C
	Junction temperature	Tj	125	°C
	Collector-emitter voltage	VCEO	80	V
	Emitter-collector voltage	VECO	7	V
	Collector current	\ \Ic	50	mA
Detector	Peak collector current (10 ms pulse, 100 pps)	I _{CP}	100	mA
De	Power dissipation	Pc	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔPC/°C	-1.5	mW/°C
	Junction temperature		125	°C
Stor	age temperature range	T _{stg}	-55 to 125	°C
Оре	rating temperature range	Topr	-55 to 100	°C
Lea	d soldering temperature (10 s)	T _{sol}	260	°C
Tota	l package power dissipation	Рт	200	mW
Tota dera	al package power dissipation (Ta ≥ 25°C)	ΔP _T /°C	-2.0	mW/°C
	ation voltage , 60 s, R.H. ≤ 60%) (Note 1)	BVs	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Device considered a two terminal device: Pins1, 3 shorted together and pins 4, 6 shorted together.

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Recommended Operating Conditions

Characteristic	Symbol	Min	Тур.	Max	Unit
Supply voltage	Vcc	_	5	48	V
Forward current	lF	_	1.6	20	mA
Collector current	Ic	_	1	10	mA
Operating temperature	Topr	-25	_	75	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
	Forward voltage	VF	IF = 10 mA	1.0	1.15	1.3	V
ED	Reverse Current	I _R	V _R = 5 V	-(()	10	μΑ
	Capacitance	Ст	V = 0 V, f = 1 MHz		30		pF
	Collector-emitter breakdown voltage	V _(BR) CEO	I _C = 0.5 mA	80)		V
ō	Emitter-collector breakdown voltage	V _{(BR)ECO}	IE = 0.1 mA	7)	_		V
Detector	Collector dark current	1	VcE = 48 V)	10	100	nA
Collector dark current	ICEO	VcE = 48 V, Ta = 85°C) —	2	50	μΑ	
	Capacitance collector to emitter	CCE	V = 0 V, f = 1 MHz	_	12	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Current transfer ratio	Ic/I _F	I _F = 1 mA, V _{CE} = 0.5 V		100	-	1200	%
Current transfer fatto)) 10/16		Rank BV	200	_	1200	/0
Low input CTR	lo/le#	$I_F = 0.5 \text{ mA}, V_{CE} = 1.5 \text{ V}$		50	_	-	%
Low Input CTR	IC/IF(low)		Rank BV	100	_	-	70
		IC = 0.5 mA, I _F = 1 mA		_	_	0.4	
Collector-emitter saturation voltage	VCE(sat)	I _C = 1 mA, I _F = 1 mA		_	0.2	1	V
Z/\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	\wedge	>	Rank BV	_	_	0.4	
Off-state collector current	(C(off)	$V_F = 0.7 \text{ V}, V_{CE} = 48 \text{ V}$		_	_	10	μΑ

Coupled Electrical Characteristics (Ta = -25 to 75°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Output to a star and a	lo/In	IF = 1 mA, VCE = 0.5 V	50	_	_	%
Current transfer ratio	IC/IF	Rank BV	100	_	_	%
Low input CTR	lo/le#	$I_F = 0.5 \text{ mA}, V_{CE} = 1.5 \text{ V}$	_	50	_	%
Low Input CTK	IC/IF(low)	Rank BV	_	100	_	%

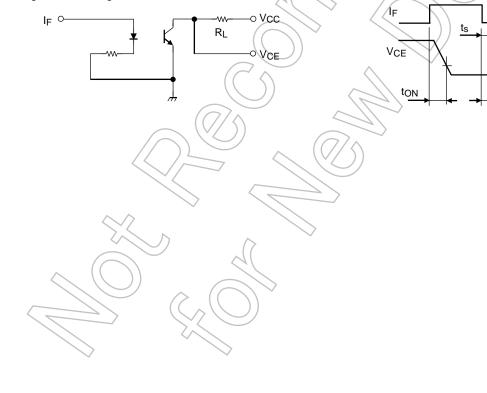
Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance (input to output)	Cs	V _S = 0 V, f = 1 MHz	_	0.8	١	pF
Isolation resistance	Rs	Vs = 500 V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	_	Ω
Isolation voltage		AC, 60 s	3750	_	_	V _{rms}
	BVS	AC, 1 s, in oil	((10000		vrms
		DC, 60 s, in oil	7	10000	_	V _{dc}

Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Rise time	t _r	40	_	8	7	
Fall time	t _f	Vcc = 10 V, Ic = 2 mA	- /	8	_	
Turn-on time	toN	R _L = 100 Ω (//)	-(()10_	_	μs
Turn-off time	toff		(-)	(8)	/ –	
Turn-on time	toN		7 -) 10	_	
Storage time	ts	$R_L = 4.7 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V, IF} = 1.6 \text{ mA}$	/)	50	_	μs
Turn-off time	toff	VCC - 5 V, IF - 1.0 IIIA		300	_	

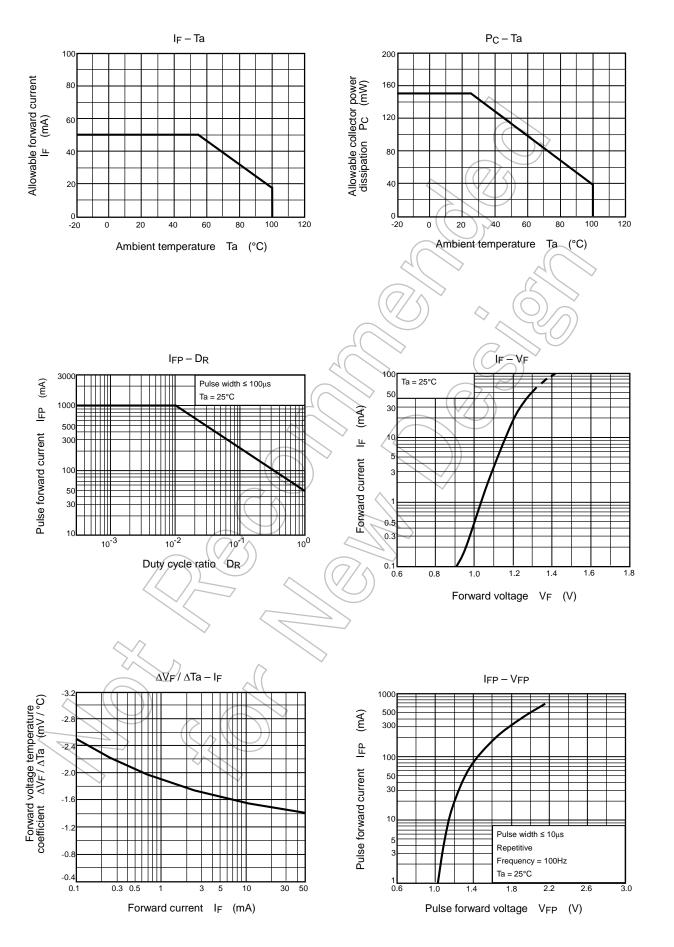
Fig. 1 Switching time test circuit

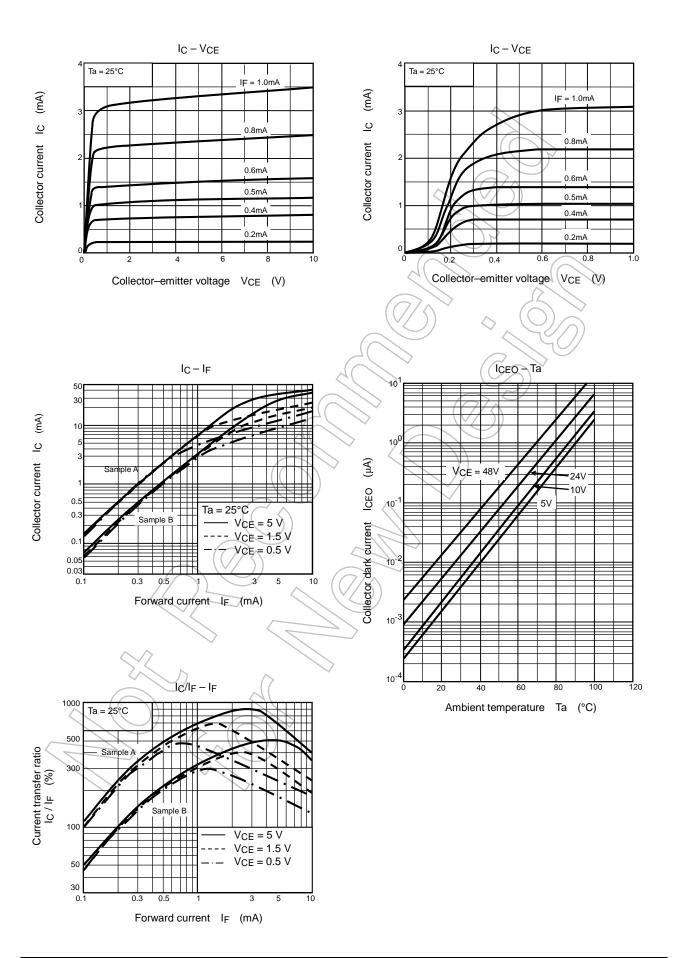


Vcc 4.5V

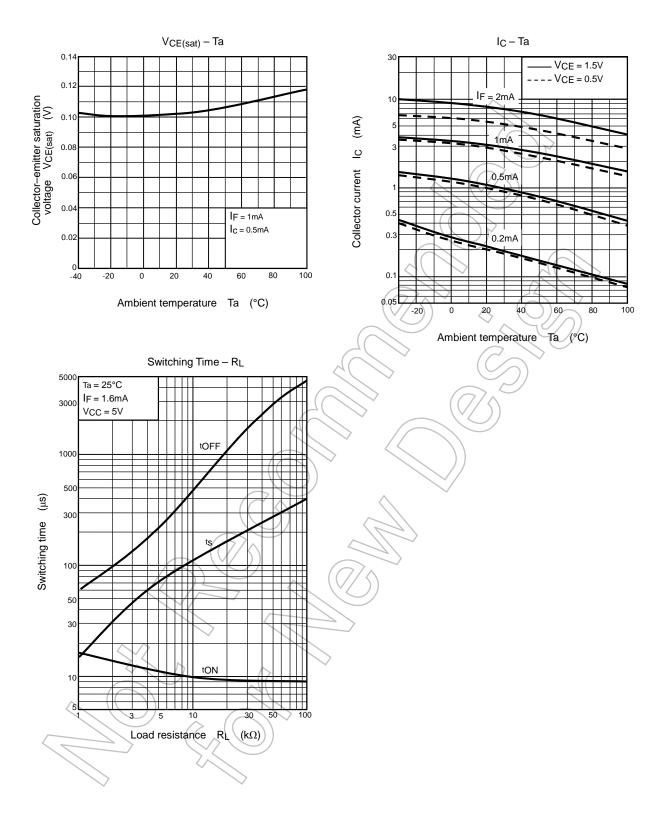
0.5V

toff





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